



Dual N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
30	$0.022 \text{ at V}_{GS} = 10 \text{ V}$	7.5		
	0.030 at V _{GS} = 4.5 V	6.5		

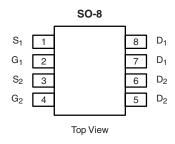
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- PWM Optimized
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



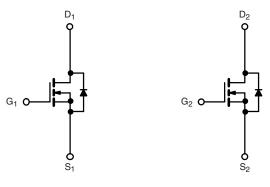
APPLICATIONS

• Symmetrical Buck-Boost DC/DC Converter



Ordering Information: Si4804BDY-T1-E3 (Lead (Pb)-free)

Si4804BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	30		V	
Gate-Source Voltage		V _{GS}	± 20			
Continuous Drain Current /T 150 °C\a	T _A = 25 °C	- I _D	7.5	5.7		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		6.0	4.6		
Pulsed Drain Current		I _{DM}	30		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	1.7	0.9		
Single Pulse Avalanche Current	1 0.1 mll	I _{AS}	10		1	
Single Pulse Avalanche Energy	L = 0.1 mH E _{AS}		5		mJ	
Mariana Dania Birahada	T _A = 25 °C	P _D	2.0	1.1	W	
Maximum Power Dissipation ^a	T _A = 70 °C] 'D	1.3	0.7] **	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
			Limits			
Parameter		Symbol	Тур.	Max.	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 10 s	- R _{thJA}	52	62.5	°C/W	
Maximum Junction-to-Ambient ²	Steady State		93	110		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	35	40		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

Si4804BDY

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MOSFET SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions Min.		Typ. ^a	Max.	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.8		3.0	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zava Cata Valtaga Dvain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	1		1	
Zero Gate Voltage Drain Current		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			15	μΑ
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α
D : 0	В	V _{GS} = 10 V, I _D = 7.5 A		0.017	0.022	0
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 6.5 A		0.024	0.030	Ω
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 7.5 A		19		S
Diode Forward Voltage ^b	V_{SD}	I _S = 1 A, V _{GS} = 0 V		0.75	1.2	V
Dynamic ^a						
Total Gate Charge	Q_g			7	11	
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 7.5 \text{ A}$		2.9		nC
Gate-Drain Charge	Q_{gd}			2.5		
Gate Resistance	R_{g}		0.5	1.5	2.6	Ω
Turn-On Delay Time	t _{d(on)}			9	15	
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		10	17	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		19	30	ns
Fall Time	t _f			9	15	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.7 A, dI/dt = 100 A/μs		35	55	

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

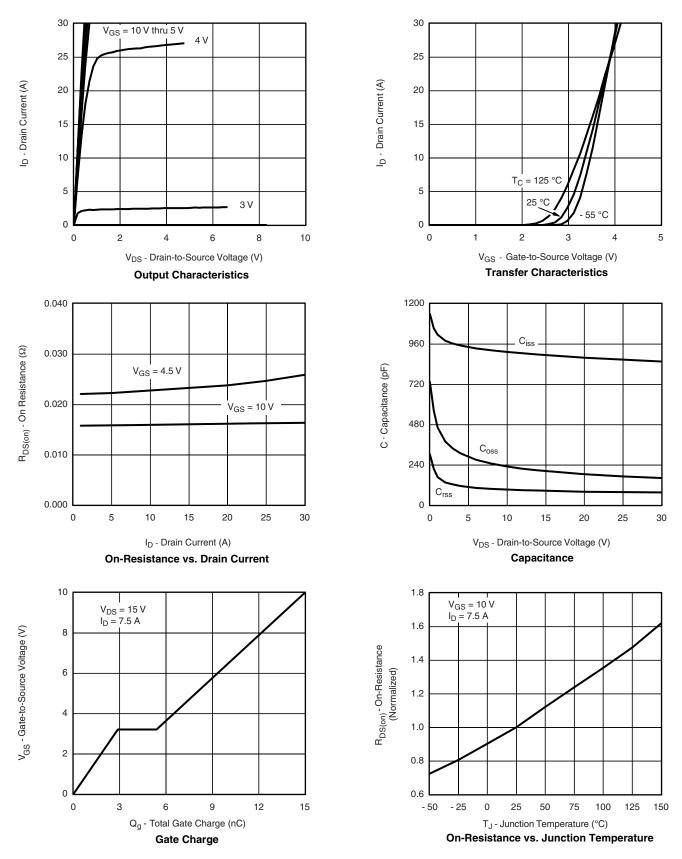
a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.





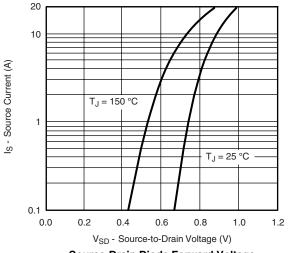
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

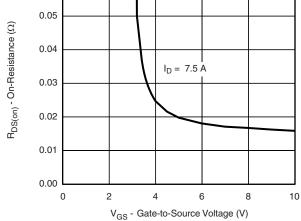


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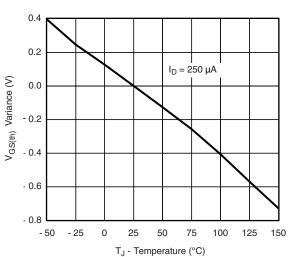
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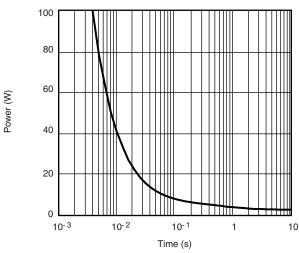
0.06

Source-Drain Diode Forward Voltage

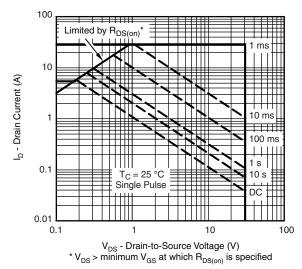


Threshold Voltage

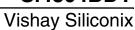
On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

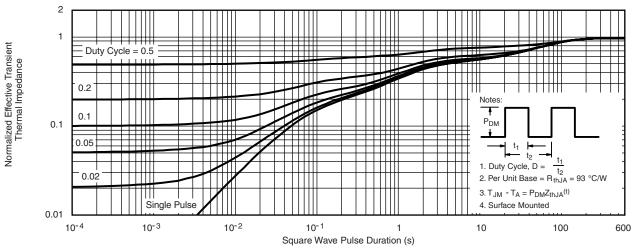


Safe Operating Area, Junction-to-Foot

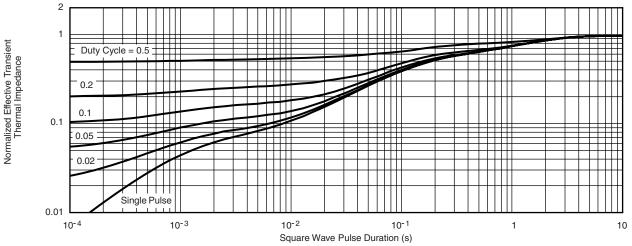




TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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